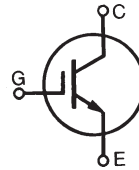


HiPerFAST™ IGBT

C2-Class High Speed IGBTs

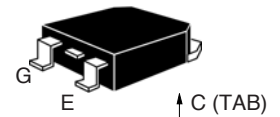
IXGH 40N60C2
IXGT 40N60C2

$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 75 \text{ A} \\ V_{CE(sat)} &= 2.7 \text{ V} \\ t_{fi typ} &= 32 \text{ ns} \end{aligned}$$

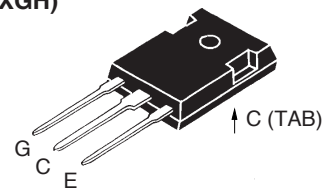


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (limited by leads)	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	40	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	200	A
SSOA	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$	$I_{CM} = 80$	A
(RBSOA)	Clamped inductive load @ $\leq 600 \text{ V}$		
P_C	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Plastic body		200	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10Nm/lb.in.	
Weight		TO-247	6 g
		TO-268	4 g

TO-268 (IXGT)



TO-247 (IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- Very high frequency IGBT
- Square RBSOA
- High current handling capability
- MOS Gate turn-on - drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

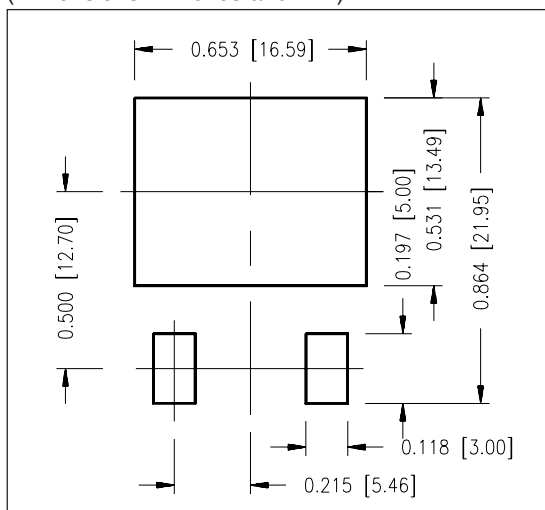
Advantages

- High power density
- Very fast switching speeds for high frequency applications

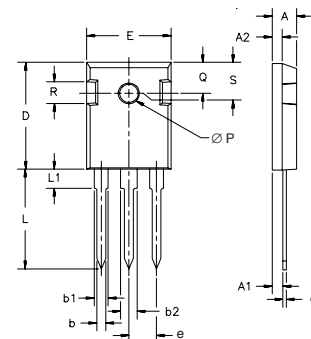
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$			50 μA 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 30 \text{ A}, V_{GE} = 15 \text{ V}$		$T_J = 25^\circ\text{C}$ 2.2 $T_J = 150^\circ\text{C}$ 2.0	2.7 V V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = 30\text{ A}; V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	20	36	S
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		2500	pF
C_{oes}			180	pF
C_{res}			54	pF
Q_g	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 300\text{ V}$		95	nC
Q_{ge}			14	nC
Q_{gc}			36	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}, R_G = R_{off} = 3\text{ }\Omega$		18	ns
t_{ri}			20	ns
$t_{d(off)}$			90	ns
t_{fi}			32	ns
E_{off}			0.20	0.37 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}, R_G = R_{off} = 3\text{ }\Omega$		18	ns
t_{ri}			20	ns
E_{on}			0.3	mJ
$t_{d(off)}$			130	ns
t_{fi}			80	ns
E_{off}			0.50	mJ
R_{thJC}				0.42 KW
R_{thCK}	(TO-247)		0.25	KW

Min. Recommended Footprint (Dimensions in inches and mm)

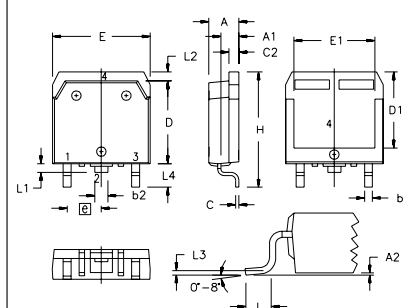


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

Fig. 1. Output Characteristics
@ 25 Deg. C

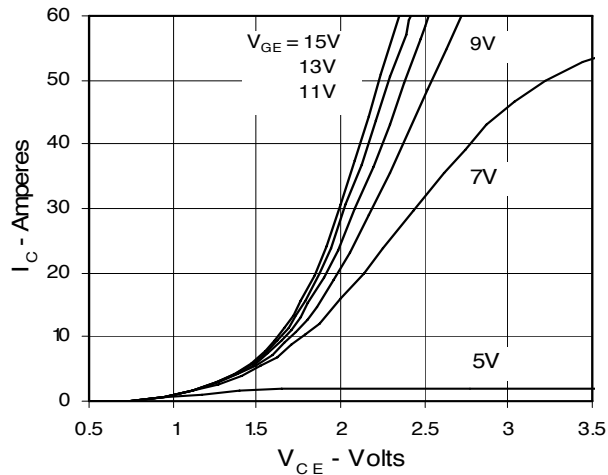


Fig. 2. Extended Output Characteristics
@ 25 deg. C

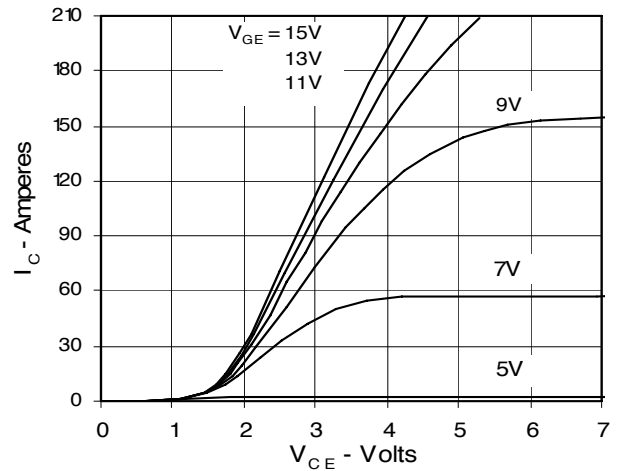


Fig. 3. Output Characteristics
@ 125 Deg. C

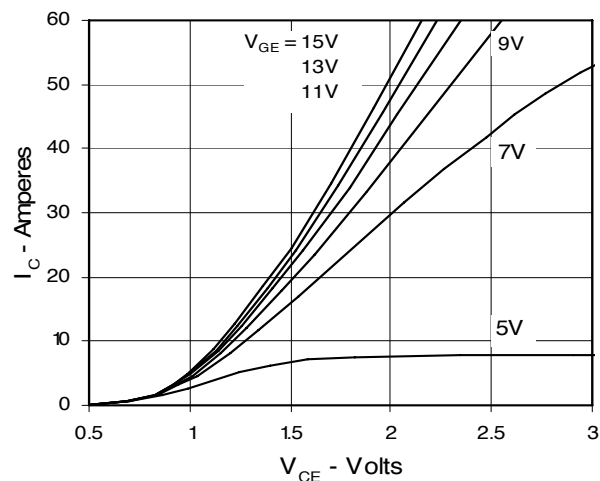


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

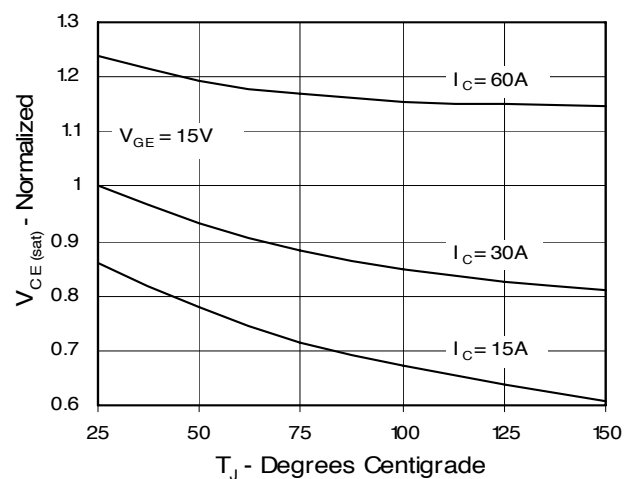


Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter voltage

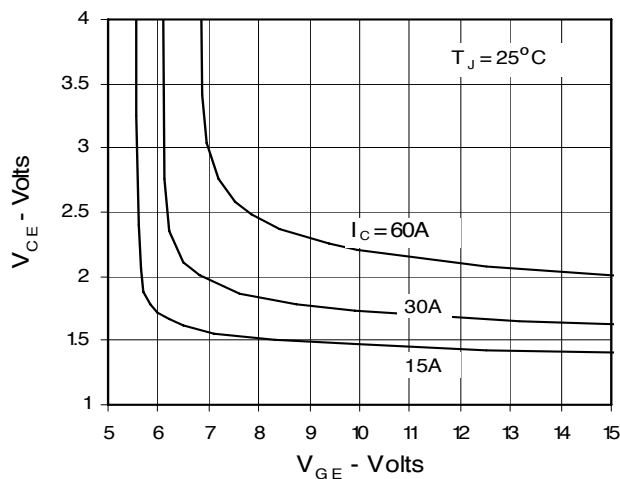


Fig. 6. Input Admittance

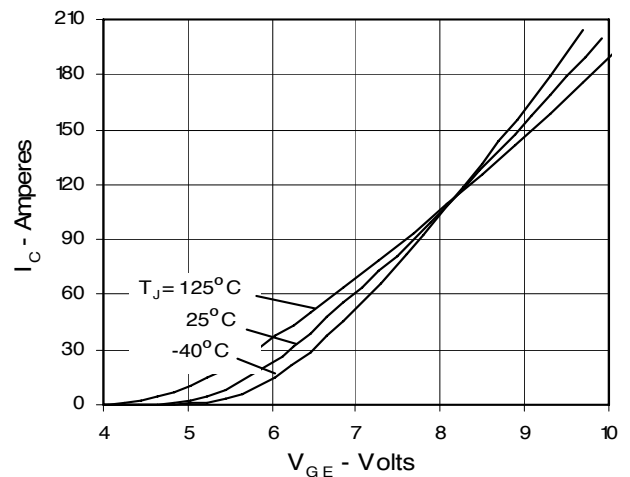


Fig. 7. Transconductance

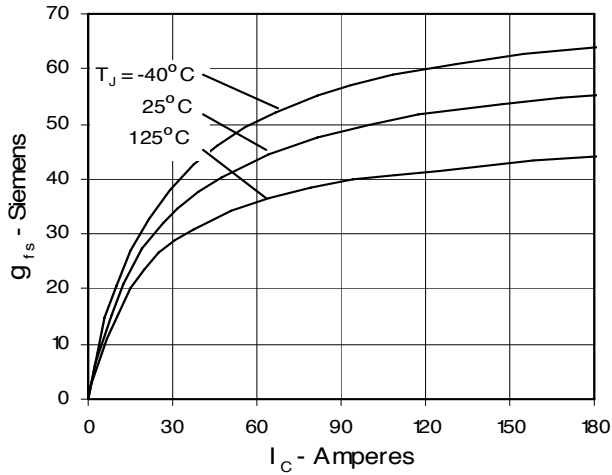


Fig. 8. Dependence of E_{off} on R_G

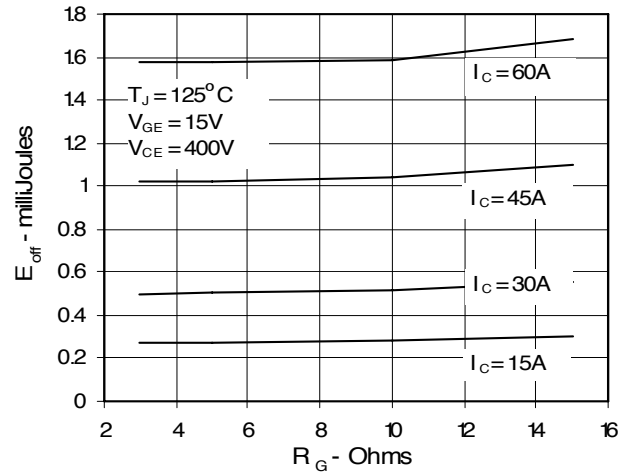


Fig. 9. Dependence of E_{off} on I_C

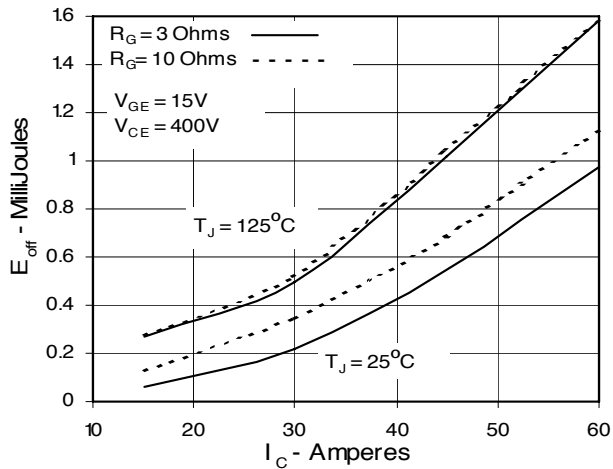


Fig. 10. Dependence of E_{off} on Temperature

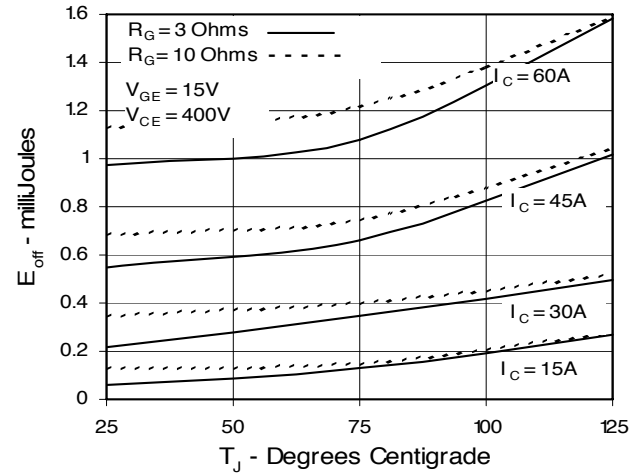


Fig. 11. Gate Charge

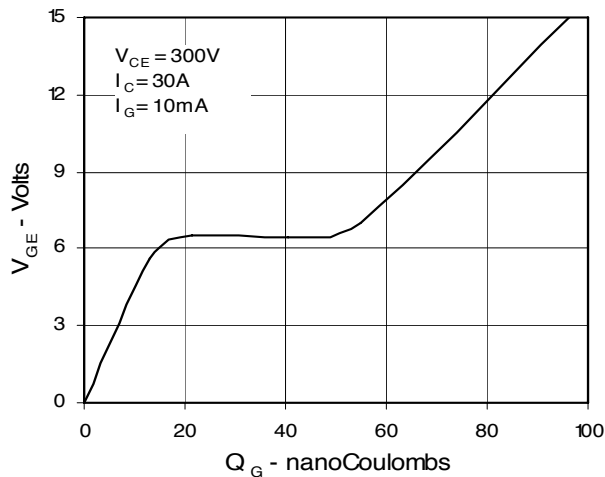


Fig. 12. Capacitance

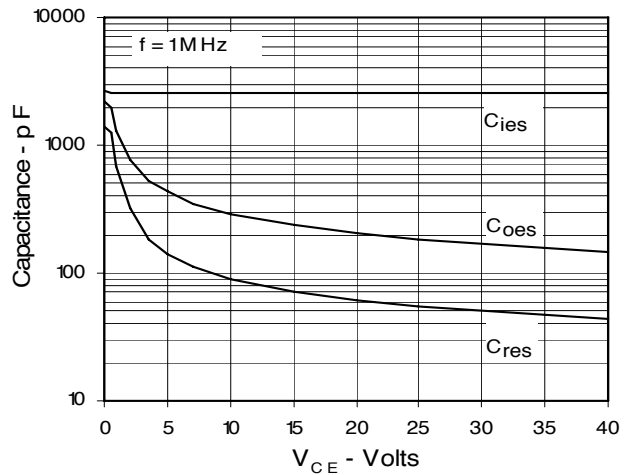


Fig. 13. Maximum Transient Thermal Resistance

